

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor device comprising:

a substrate including a plurality of holes and a surface over which an interconnecting pattern is formed, part of the interconnecting pattern being superposed over the holes, the interconnecting pattern not formed on inner surfaces of the holes;

a semiconductor chip disposed over another surface of the substrate and including a plurality of electrodes to be positioned over the holes; and

conductive posts provided contiguously on the electrodes and within the holes to be electrically connected to the interconnecting pattern.

2. (Original) The semiconductor device as defined in claim 1,

wherein a resin is provided between the substrate and the semiconductor chip.

3. (Previously Amended) The semiconductor device as defined in claim 2,

wherein the resin is an anisotropic conductive material containing conductive particles; and

wherein the conductive posts are electrically connected to the interconnecting pattern through the conductive particles.

4. (Original) The semiconductor device as defined in claim 1,

wherein part of the interconnecting pattern closes the holes.

5. (Original) The semiconductor device as defined in claim 1,

wherein the interconnecting pattern includes a plurality of interconnecting lines; and

wherein two or more interconnecting lines extend over each of the holes.

6. (Original) The semiconductor device as defined in claim 1,

wherein the other surface of the substrate is roughed.

7. (Previously Amended) A semiconductor device comprising:

a substrate including a plurality of holes and a surface over which an interconnecting pattern is formed, part of the interconnecting pattern being superposed over the holes;

a semiconductor chip disposed over another surface of the substrate and including a plurality of electrodes to be positioned over the holes; and

conductive members provided within the holes for electrically connecting the electrodes to the interconnecting pattern,

wherein a recognition hole is formed in the substrate at a position differing from the holes; and

wherein a recognition pattern is formed over the recognition hole on the side of a surface of the substrate including the interconnecting pattern.

8. (Original) The semiconductor device as defined in claim 7,

wherein the recognition hole is formed in the substrate outside a mounting region for the semiconductor chip.

9. (Original) The semiconductor device as defined in claim 7,

wherein the recognition pattern includes:

a first pattern extending in the X-axis direction of the two-dimensional coordinate system established on a surface of the substrate; and

a second pattern extending in the Y-axis direction.

10. (Previously Amended) The semiconductor device as defined in claim 1,

wherein the conductive posts are a plurality of layered bumps.

11. (Original) The semiconductor device as defined in claim 10,

wherein the bumps include first bumps formed on the electrodes and second bumps formed on the first bumps.

12. (Original) The semiconductor device as defined in claim 11,

wherein at least the first bumps are ball bumps.

13. (Previously Amended) A semiconductor device comprising:

a substrate including a plurality of holes and a surface over which an interconnecting pattern is formed, part of the interconnecting pattern being superposed over the holes;

a semiconductor chip disposed over another surface of the substrate and including a plurality of electrodes to be positioned over the holes; and

conductive members provided within the holes for electrically connecting the electrodes to the interconnecting pattern,

wherein the conductive members are a plurality of layered bumps,

wherein the bumps include first bumps formed on the electrodes and second bumps formed on the first bumps,

wherein the second bumps are formed of a metal which has a melting point lower than the melting point of the first bumps.

14. (Original) The semiconductor device as defined in claim 13,

wherein the first bumps are formed of gold.

15. (Original) The semiconductor device as defined in claim 14,

wherein the second bumps are formed of solder.

16. (Original) The semiconductor device as defined in claim 11,

wherein the first bumps and the second bumps are formed of the same material.

17. (Previously Amended) The semiconductor device as defined in claim 1,

wherein the semiconductor chip is mounted face-down to the substrate.

18. (Previously Amended) A circuit board over which is mounted the semiconductor device as defined in claim 1.

19. (Previously Amended) An electronic instrument provided with the semiconductor device as defined in claim 1.

20-32. (Withdrawn).

33. (Previously Added) The semiconductor device as defined in claim 1,

wherein there is a space between each of the conductive posts and an inner surface of each of the holes.

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